

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A display device comprising:

a substrate;

a scanning signal line formed over the substrate;

an insulating film formed over the substrate and the scanning signal line;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the scanning signal line comprises a first metal film and an ~~aluminum~~ a second metal film formed over the first metal film, the ~~aluminum~~ second metal film having an ~~upper~~ a top surface with a width that is smaller than a width of a lower bottom surface of the first metal film at least in a crossover portion of the scanning signal line and the image signal line.

Claims 2-13 (Canceled).

14. (Withdrawn) A display device comprising:

a substrate;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise an aluminum film, and the drain and source electrodes are disposed such that a spacing between a lower surface of the drain electrode and a lower surface of the source electrode over the semiconductor film is smaller than a spacing between an upper surface of the drain electrode and an upper surface of the source electrode over the semiconductor film, and

wherein the gate electrode comprises an aluminum film, the aluminum film being dimensioned to cover a plan view area of a principal surface of the substrate larger than an area covered by the semiconductor film.

15. (Withdrawn) A display device comprising:

a substrate;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise a high

melting point metal film and an aluminum film formed over the high melting point metal film, and

wherein the gate electrode comprises an aluminum film,
the aluminum film being dimensioned to cover a plan view area of a principal surface of the substrate larger than an area covered by the semiconductor film.

16. (Withdrawn) A liquid crystal display device according to claim 15,

wherein the high melting point metal film comprises Mo, Ti, Ta, W, or silicide of one of them.

17. (Withdrawn) A liquid crystal display device according to claim 15,

wherein the pixel electrode contacts the high melting point metal film.

18. (Withdrawn) A liquid crystal display device according to claim 15,

wherein the pixel electrode contacts the aluminum film.

19. (Withdrawn) A display device comprising:

a substrate;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise a high

melting point metal film and an aluminum film formed over the high melting point metal film, and the high melting point metal film and the aluminum film of both the source and drain electrodes are disposed such that a spacing between a lower surface of the high melting point metal film of the drain electrode and a lower surface of the high melting point metal film of the source electrode over the semiconductor film is smaller than a spacing between an upper surface of the aluminum film of the drain electrode and an upper surface of the aluminum film of the source electrode over the semiconductor film, and

wherein the gate electrode comprises an aluminum film, the aluminum film being dimensioned to cover a plan view area of a principal surface of the substrate larger than an area covered by the semiconductor film.

20. (Withdrawn) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise an aluminum film, and the drain and source electrodes are disposed such that a spacing between a lower surface of the drain electrode and a lower surface of the source electrode

over the semiconductor film is smaller than a spacing between an upper surface of the drain electrode and an upper surface of the source electrode over the semiconductor film, and

wherein the gate electrode and the scanning signal line comprise an aluminum film, and the scanning signal line has an upper surface with a width that is smaller than a width of a lower surface of the scanning signal line.

21. (Withdrawn) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise a high melting point metal film and an aluminum film formed over the high melting point metal film, and

wherein the gate electrode and the scanning signal line comprise an aluminum film, and the scanning signal line has an upper surface with a width that is smaller than a width of a lower surface of the scanning signal line.

22. (Withdrawn) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,

wherein the drain electrode and the source electrode comprise a high melting point metal film and an aluminum film formed over the high melting point metal film, and the high melting point metal film and the aluminum film of both the source and drain electrodes are disposed such that a spacing between a lower surface of the high melting point metal film of the drain electrode and a lower surface of the high melting point metal film of the source electrode over the semiconductor film is smaller than a spacing between an upper surface of the aluminum film of the drain electrode and an upper surface of the aluminum film of the source electrode over the semiconductor film, and

wherein the gate electrode and the scanning signal line comprise an aluminum film, and the scanning signal line having an upper surface with a width that is smaller than a width of a lower surface of the scanning signal line.

23. (New) A display device according to claim 1,

wherein the second metal film is an aluminum film.

24. (New) A display device according to claim 1,
wherein the image signal line is formed over the insulating film.

25. (New) A display device according to claim 24,
wherein the second metal film is an aluminum film.

26. (New) A display device comprising:
a substrate;
a scanning signal line;
an insulating film formed over the substrate;
an image signal line;
a pixel electrode; and
a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode,
wherein the scanning signal line comprises a first metal film and an aluminum film formed over the first metal film, the aluminum film having a top surface with a width that is smaller than a width of a bottom surface of the first metal film at least in a crossover portion of the scanning signal line and the image signal line.

27. (New) A display device according to claim 26,
wherein the image signal line is formed over the insulating film.

28. (New) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film comprising a channel region formed over the insulating film, a drain electrode electrically connected to the image signal line, and a source electrode electrically connected to the pixel electrode;

wherein the scanning signal line comprises a first metal film and an aluminum film, the scanning signal line having a top surface with a width that is smaller than a width of a bottom surface of the scanning signal line at least in a crossover portion of the scanning signal line and the image signal line.

29. (New) A display device according to claim 28,

wherein the image signal line is formed over the insulating film.

30. (New) A display device according to claim 28,

wherein the aluminum film is formed over the first metal film.

31. (New) A display device comprising:

a substrate;

a scanning signal line;

an insulating film formed over the substrate;

an image signal line;

a pixel electrode formed over the substrate; and

a thin film transistor comprising a gate electrode connected to the scanning signal line and formed between the substrate and the insulating film, a semiconductor film comprising a channel region formed over the insulating film, and an electrode electrically connected to the image signal line,

wherein the scanning signal line comprises a first metal film and a second metal film formed over the first metal film, the second metal film having a top surface with a width that is smaller than a width of a bottom surface of the first metal film at least in a crossover portion of the scanning signal line and the image signal line.

32. (New) A display device according to claim 31,

wherein the second metal film is an aluminum film.